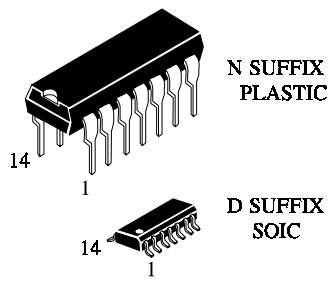


IW4013B

Dual D Flip-Flop
High-Voltage Silicon-Gate CMOS

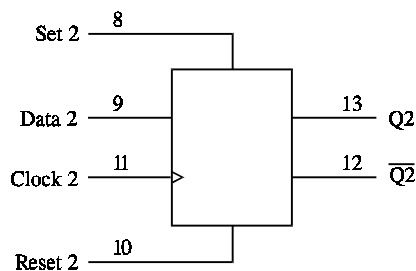
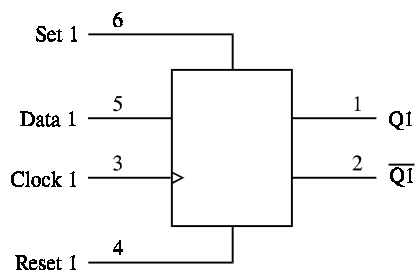
The IW4013B consists of two identical, independent data-type flip-flops. Each flip-flop has independent data, set, reset, and clock inputs and Q and \bar{Q} outputs. These devices can be used for shift register applications, and, by connecting Q output to the data input, for counter and toggle applications. The logic level present at the D input is transferred to the Q output during the positive-going transition of the clock pulse. Setting or resetting is independent of the clock and is accomplished by a high level on the set or reset line, respectively.

- Operating Voltage Range: 3.0 to 18 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):
 - 1.0 V min @ 5.0 V supply
 - 2.0 V min @ 10.0 V supply
 - 2.5 V min @ 15.0 V supply



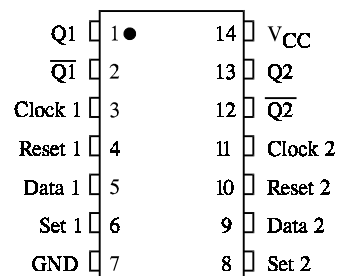
ORDERING INFORMATION
 IW4013BN Plastic
 IW4013BD SOIC
 $T_A = -55^\circ$ to 125° C for all packages

LOGIC DIAGRAM



PIN 14 = V_{CC}
 PIN 7 = GND

PIN ASSIGNMENT



FUNCTION TABLE

Inputs				Outputs	
Clock	Data	Reset	Set	Q	\bar{Q}
	L	L	L	L	H
	H	L	L	H	L
	X	L	L	Q	\bar{Q}
X	X	H	L	L	H
X	X	L	H	H	L
X	X	H	H	H	H

X = don't care

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +20	V
V _{IN}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
V _{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
I _{IN}	DC Input Current, per Pin	±10	mA
P _D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
P _D	Power Dissipation per Output Transistor	100	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.

+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	3.0	18	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-55	+125	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND ≤ (V_{IN} or V_{OUT}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}).
Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				≥-55°C	25°C	≤125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{OUT} =0.5 V or V _{CC} - 0.5 V	5.0	3.5	3.5	3.5	V
		V _{OUT} =1.0 V or V _{CC} - 1.0 V	10	7	7	7	
		V _{OUT} =1.5 V or V _{CC} - 1.5 V	15	11	11	11	
V _{IL}	Maximum Low -Level Input Voltage	V _{OUT} =0.5 V or V _{CC} - 0.5 V	5.0	1.5	1.5	1.5	V
		V _{OUT} =1.0 V or V _{CC} - 1.0 V	10	3	3	3	
		V _{OUT} =1.5 V or V _{CC} - 1.5 V	15	4	4	4	
V _{OH}	Minimum High-Level Output Voltage	V _{IN} =GND or V _{CC}	5.0	4.95	4.95	4.95	V
			10	9.95	9.95	9.95	
			15	14.95	14.95	14.95	
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} =GND or V _{CC}	5.0	0.05	0.05	0.05	V
			10	0.05	0.05	0.05	
			15	0.05	0.05	0.05	
I _{IN}	Maximum Input Leakage Current	V _{IN} = GND or V _{CC}	18	±0.1	±0.1	±1.0	µA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{IN} = GND or V _{CC}	5.0	1	1	30	µA
			10	2	2	60	
			15	4	4	120	
			20	20	20	600	
I _{OL}	Minimum Output Low (Sink) Current	V _{IN} = GND or V _{CC} U _{OL} =0.4 V U _{OL} =0.5 V U _{OL} =1.5 V	5.0	0.64	0.51	0.36	mA
			10	1.6	1.3	0.9	
			15	4.2	3.4	2.4	
I _{OH}	Minimum Output High (Source) Current	V _{IN} = GND or V _{CC} U _{OH} =2.5 V U _{OH} =4.6 V U _{OH} =9.5 V U _{OH} =13.5 V	5.0	-2.0	-1.6	-1.15	mA
			5.0	-0.64	-0.51	-0.36	
			10	-1.6	-1.3	-0.9	
			15	-4.2	-3.4	-2.4	

AC ELECTRICAL CHARACTERISTICS($C_L=50\text{pF}$, $R_L=200\text{ k}\Omega$, Input $t_r=t_f=20\text{ ns}$)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			≥-55°C	25°C	≤125°C	
f _{max}	Maximum Clock Frequency (Figure 1)	5.0	3.5	3.5	1.75	MHz
		10	8	8	4	
		15	12	12	6	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q or \bar{Q} (Figure 1)	5.0	300	300	600	ns
		10	130	130	260	
		15	90	90	180	
t _{PLH}	Maximum Propagation Delay, Set to Q or Reset to Q (Figure 2)	5.0	300	300	600	ns
		10	130	130	260	
		15	90	90	180	
t _{PHL}	Maximum Propagation Delay, Set to \bar{Q} or Reset to \bar{Q} (Figure 2)	5.0	400	400	800	ns
		10	170	170	340	
		15	120	120	240	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figure 1)	5.0	200	200	400	ns
		10	100	100	200	
		15	80	80	160	
C _{IN}	Maximum Input Capacitance	-		7.5		pF

TIMING REQUIREMENTS($C_L=50\text{pF}$, $R_L=200\text{ k}\Omega$, Input $t_r=t_f=20\text{ ns}$)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			≥-55°C	25°C	≤125°C	
t _w	Minimum Pulse Width, Clock (Figure 1)	5.0	140	140	280	ns
		10	60	60	120	
		15	40	40	80	
t _w	Minimum Pulse Width, Set or Reset (Figure 2)	5.0	180	180	360	ns
		10	80	80	160	
		15	50	50	100	
t _{su}	Minimum Setup Time, Data to Clock (Figure 3)	5.0	40	40	80	ns
		10	20	20	40	
		15	15	15	30	
t _h	Minimum Hold Time, Clock to Data (Figure 3)	5.0	5	5	10	ns
		10	5	5	10	
		15	5	5	10	
t _r , t _f	Maximum Input Rise or Fall Time, Clock (Figure 1)	5.0	500	500	1000	μs
		10	30	30	60	
		15	6	6	12	

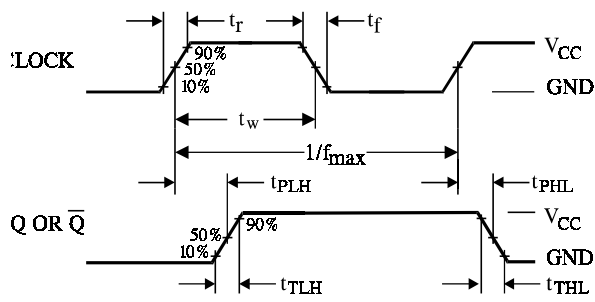


Figure 1. Switching Waveforms

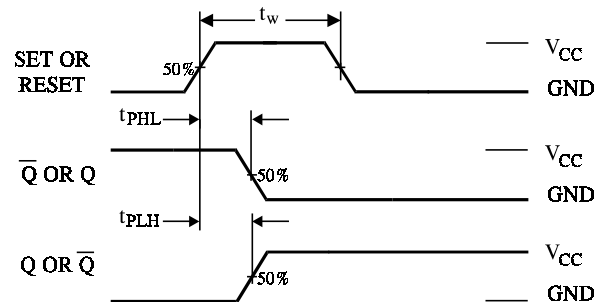


Figure 2. Switching Waveforms

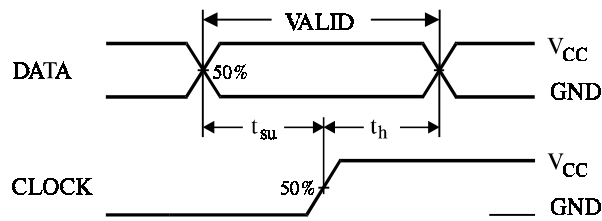


Figure 3. Switching Waveforms

**EXPANDED LOGIC DIAGRAM
(1/2 of the Device)**

